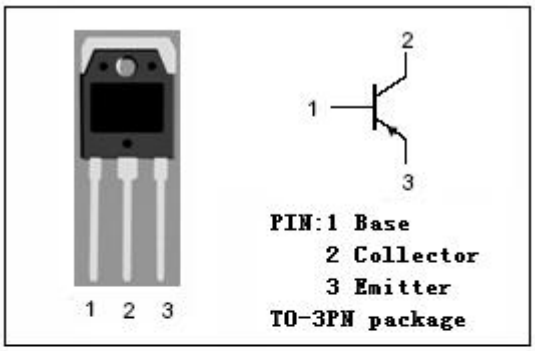
# *isc* Silicon PNP Power Transistor — 2SB816

## DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -120V(Min)
- Good Linearity of $h_{FE}$
- Wide Area of Safe Operation
- Complement to Type 2SD1046
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

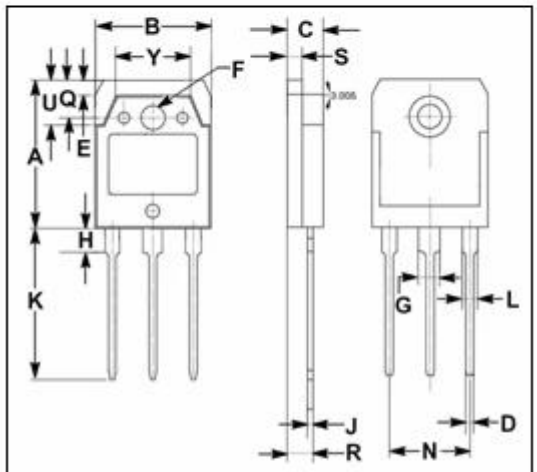



## APPLICATIONS

- Designed for LF power amplifier, 50W output large power switching applications.

## ABSOLUTE MAXIMUM RATINGS($T_a$=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{CBO}$ | Collector-Base Voltage | -150 | V |
| $V_{CEO}$ | Collector-Emitter Voltage | -120 | V |
| $V_{EBO}$ | Emitter-Base Voltage | -6 | V |
| $I_C$ | Collector Current-Continuous | -8 | A |
| $I_{CP}$ | Collector Current-Pulse | -12 | A |
| $P_C$ | Collector Power Dissipation @ $T_C$=25℃ | 80 | W |
| $T_J$ | Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature Range | -40~150 | ℃ |




| DIM | mm MIN | mm MAX |
|---|---|---|
| A | 19.60 | 20.10 |
| B | 15.50 | 15.70 |
| C | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| H | 3.20 | 3.40 |
| J | 0.595 | 0.605 |
| K | 20.00 | 20.70 |
| L | 1.90 | 2.20 |
| N | 10.89 | 10.91 |
| Q | 4.90 | 5.10 |
| R | 3.35 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.10 |
| Y | 9.90 | 10.10 |

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## ELECTRICAL CHARACTERISTICS

**$T_C$=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C$= -30mA ; $R_{BE}$=∞ | -120 | | | V |
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C$= -5mA; $I_E$= 0 | -150 | | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E$= -5mA; $I_C$= 0 | -6 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C$= -5.0A; $I_B$= -0.5A | | | -2.0 | V |
| $V_{BE(on)}$ | Base -Emitter On Voltage | $I_C$= -1A; $V_{CE}$= -5V | | | -1.5 | V |
| $I_{CBO}$ | Collector Cutoff Current | $V_{CB}$= -80V; $I_E$=0 | | | -100 | μA |
| $I_{EBO}$ | Emitter Cutoff Current | $V_{EB}$= -4V; $I_C$=0 | | | -100 | μA |
| $h_{FE-1}$ | DC Current Gain | $I_C$= -1A; $V_{CE}$= -5V | 60 | | 200 | |
| $h_{FE-2}$ | DC Current Gain | $I_C$= -5A; $V_{CE}$= -5V | 20 | | | |

◆ **$h_{FE-1}$ Classifications**

| D | E |
|---|---|
| 60-120 | 100-200 |

**NOTICE：**

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